SCLS229H - OCTOBER 1995 - REVISED JANUARY 2000

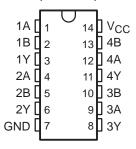
- **EPIC™** (Enhanced-Performance Implanted **CMOS) Process**
- Inputs Are TTL-Voltage Compatible
- Latch-Up Performance Exceeds 250 mA Per **JESD 17**
- **ESD Protection Exceeds 2000 V Per** MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- **Package Options Include Plastic** Small-Outline (D), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Standard Plastic (N) and Ceramic (J) **DIPs**

description

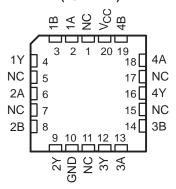
The 'AHCT00 devices perform the Boolean function $Y = \overline{A} \cdot \overline{B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

The SN54AHCT00 is characterized for operation over the full military temperature range of -55°C to 125°C. The SN74AHCT00 is characterized for operation from -40°C to 85°C.

SN54AHCT00 . . . J OR W PACKAGE SN74AHCT00 . . . D, DB, DGV, N, OR PW PACKAGE (TOP VIEW)



SN54AHCT00 . . . FK PACKAGE (TOP VIEW)



NC - No internal connection

FUNCTION TABLE (each gate)

INP	JTS	OUTPUT
Α	В	Υ
Н	Н	L
L	Χ	Н
Х	L	Н



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

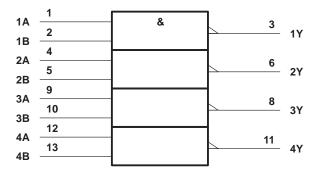
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SN54AHCT00, SN74AHCT00 QUADRUPLE 2-INPUT POSITIVE-NAND GATES

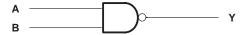
SCLS229H - OCTOBER 1995 - REVISED JANUARY 2000

logic symbol[†]



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for D, DB, DGV, J, N, PW, and W packages.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V _{CC}		
Output voltage range, VO (see Note 1)		
Input clamp current, I_{IK} ($V_I < 0$)		
Output clamp current, I _{OK} (V _O < 0 or V _O > V _C	:c)	±20 mA
Continuous output current, $I_O(V_O = 0 \text{ to } V_{CC})$	٠	±25 mA
Continuous current through V _{CC} or GND		±50 mA
Package thermal impedance, θ _{JA} (see Note 2)): D package	86°C/W
	DB package	96°C/W
	DGV package	127°C/W
	N package	80°C/W
	PW package	113°C/W
Storage temperature range, T _{stg}		–65°C to 150°C

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The package thermal impedance is calculated in accordance with JESD 51.



recommended operating conditions (see Note 3)

		SN54AI	HCT00	SN74AHCT00		UNIT
		MIN	MAX	MIN	MAX	UNIT
VCC	Supply voltage	4.5	5.5	4.5	5.5	V
VIH	High-level input voltage	2		2		V
VIL	Low-level input voltage		0.8		0.8	V
٧ _I	Input voltage	0	5.5	0	5.5	V
٧o	Output voltage	0	Vcc	0	VCC	V
IOH	High-level output current		-8		-8	mA
l _{OL}	Low-level output current		8		8	mA
Δt/Δν	Input transition rise or fall rate		20		20	ns/V
TA	Operating free-air temperature	<i>–</i> 55	125	-40	85	°C

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	vcc	T _A = 25°C			SN54AHCT00		SN74AHCT00		UNIT
PARAWETER	TEST CONDITIONS		MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
V	I _{OH} = -50 μA	4.5 V	4.4	4.5		4.4		4.4		V
VOH	I _{OH} = -8 mA	4.5 V	3.94			3.8		3.8		
Vai	I _{OL} = 50 μA	4.5 V			0.1		0.1		0.1	V
VOL	I _{OL} = 8 mA				0.36		0.44		0.44	
lj	V _I = V _{CC} or GND	0 V to 5.5 V			±0.1		±1*		±1	μΑ
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			2		20		20	μΑ
∆l _{CC} †	One input at 3.4 V, Other inputs at V _{CC} or GND	5.5 V			1.35		1.5		1.5	mA
C _i	V _I = V _{CC} or GND	5 V		2	10				10	pF

 $^{^{*}}$ On products compliant to MIL-PRF-38535, this parameter is not production tested at $V_{CC} = 0 \text{ V}$.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V \pm 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	TO (OUTPUT)	LOAD CAPACITANCE	LOAD T _A = 25°C		SN54AHCT00		SN74AHCT00		UNIT				
PARAMETER	(INPUT)			MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT			
t _{PLH}	A or B	V	C _L = 15 pF		5**	6.9**	1**	8**	1	8	ns			
tPHL		'			5**	6.9**	1**	8**	1	8				
tPLH	A or B	A an D	A or D	V /	C: 50 pF	C: 50 pF		5.5	7.9	1	9	1	9	20
tPHL		r	C _L = 50 pF		5.5	7.9	1	9	1	9	ns			

^{**} On products compliant to MIL-PRF-38535, this parameter is not production tested.



[†] This is the increase in supply current for each input at one of the specified TTL voltage levels rather than 0 V or VCC.

SN54AHCT00, SN74AHCT00 QUADRUPLE 2-INPUT POSITIVE-NAND GATES

SCLS229H - OCTOBER 1995 - REVISED JANUARY 2000

noise characteristics, V_{CC} = 5 V, C_L = 50 pF, T_A = 25°C (see Note 4)

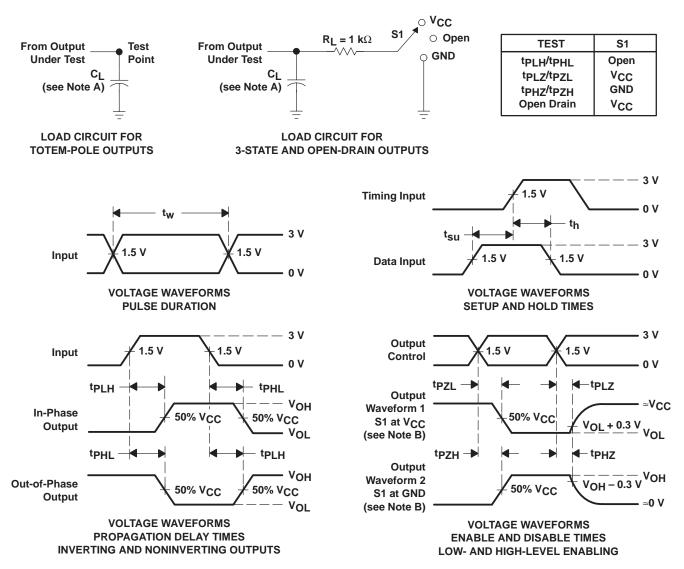
	PARAMETER				UNIT
					UNIT
V _{OL(P)}	Quiet output, maximum dynamic V _{OL}		0.4	0.8	V
V _{OL(V)}	Quiet output, minimum dynamic V _{OL}		-0.4	-0.8	V
VOH(V)	Quiet output, minimum dynamic VOH		4.5		V
VIH(D)	High-level dynamic input voltage	2			V
V _{IL(D)}	Low-level dynamic input voltage			0.8	V

NOTE 4: Characteristics are for surface-mount packages only.

operating characteristics, V_{CC} = 5 V, T_A = 25°C

	PARAMETER		NDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance	No load,	f = 1 MHz	10.5	pF

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_Q = 50 \Omega$, $t_f \leq$ 3 ns, $t_f \leq$ 3 ns.
- D. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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